

ETR0209-011

### Highly Accurate, Ultra Small, Low Power Consumption Voltage Detector

### **■**GENERAL DESCRIPTION

The XC6120 series are highly precise, low power consumption voltage detectors, manufactured using CMOS and laser trimming technologies. With low power consumption and high accuracy, the series is suitable for precision mobile equipment. The XC6120 in ultra small packages are ideally suited for high-density mounting. The XC6120 is available in both CMOS and N-channel open drain output configurations.

#### APPLICATIONS

- Microprocessor reset circuitry
- Memory battery back-up circuits
- Power-on reset circuits
- Power failure detection
- System battery life and charge voltage monitors

### **■**FEATURES

Highly Accurate :± 2% (V<sub>DF</sub>≥1.5V) :± 30mV (V<sub>DF</sub><1.5V)

**Low Power Consumption**:  $0.6 \,\mu$  A [ $\dot{V}_{DF}$ =2.7V,  $\dot{V}_{IN}$ =2.97V] **Detect Voltage Range** :  $1.0 \,\text{V} \sim 5.0 \,\text{V}$  (0.1V increments)

Operating Voltage Range: 0.7V ~ 6.0V Detect Voltage Temperature Characteristics

:±100ppm/°C (TYP.)

Output Configuration : CMOS (XC6120C)

: N-cna

: N-channel open drain (XC6120N)

Operating

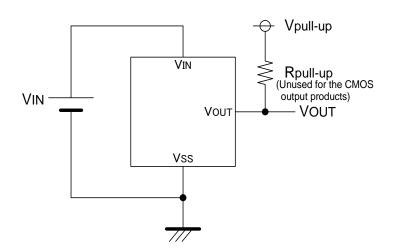
Temperature Range : -40°C~+85°C

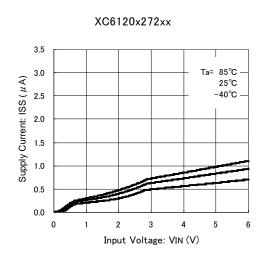
Packages : USP-3, SSOT-24, SOT-25 Environmentally Friendly : EU RoHS Compliant, Pb Free

## **■**TYPICAL APPLICATION CIRCUIT

# ■ TYPICAL PERFORMANCE CHARACTERISTICS

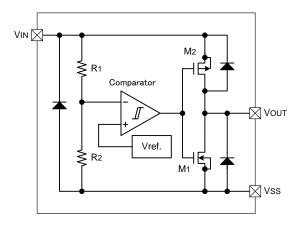
Supply Current vs. Input Voltage





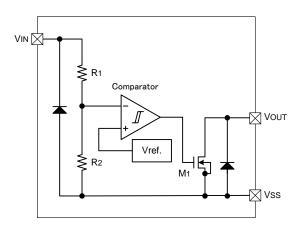
## **■BLOCK DIAGRAMS**

## (1) XC6120C



\* Diodes inside the circuits are ESD protection diodes and parasitic diodes.

### (2) XC6120N



\* Diodes inside the circuits are ESD protection diodes and parasitic diodes.

## **■PRODUCT CLASSIFICATION**

#### 1) Ordering Information

XC6120123456-7(\*1)

DESIGNATOR	ITEM	SYMBOL	DESCRIPTION
1	Output Configuration	С	CMOS output
1	Output Configuration	N	N-ch open drain output
23	Detect Voltage (V <sub>DF</sub> )	10~50	For example 1.0V → ②1, ③0
4	Detect Accuracy	2	$\pm 2\%(1.5V \leq VDF \leq 5.0V)$
4 D	Detect Accuracy	2	±30mV(1.0V≦VDF≦1.5V)
		HR	USP-3 (3,000pcs/Reel)
		HR-G	USP-3 (3,000pcs/Reel)
(₹)(*1)	Packages (Order Unit)	NR	SSOT-24 (3,000pcs/Reel)
36-7/17		NR-G	SSOT-24 (3,000pcs/Reel)
		SR-G	SOT-25 (3,000pcs/Reel) Standard feed(*2)
		SL-G	SOT-25 (3,000pcs/Reel) Reverse feed(*2)

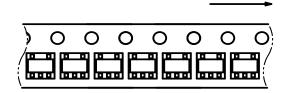
The "-G" suffix indicates that the products are Halogen and Antimony free as well as being fully EU RoHS compliant.

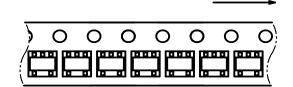
direction of feed

### 2) Taping Specifications

· SR-G

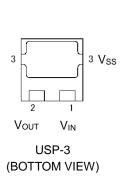


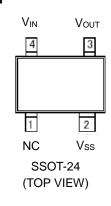


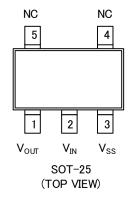


direction of feed

### **■ PIN CONFIGURATION**







## **■ PIN ASSIGNMENT**

PIN NUMBER			PIN NAME	FUNCTION	
USP-3	SSOT-24	SOT-25	PIN NAME	FUNCTION	
1	4	2	Vin	Power Input	
3	2	3	Vss	Ground	
2	3	1	$V_{OUT}$	Output (Detect "Low")	
-	1	4,5	NC	No Connection	

<sup>(\*2)</sup> SOT-25 uses Cu wires.

# XC6120 Series

## ■ ABSOLUTE MAXIMUM RATINGS

Ta=25°C

PARAMETER		SYMBOL	RATING	UNITS	
Input Voltage		V <sub>IN</sub>	Vss-0.3~7.0	V	
Out	put Current	l <sub>out</sub>	10	mA	
Output Voltage	CMOS Output	Vоит	Vss-0.3~V <sub>IN</sub> +0.3	V	
Output Voltage	N-ch Open Drain Output	VOUT	V <sub>SS</sub> -0.3~7.0		
	USP-3		120		
	USF-3	Pd	1000 (40mm x 40mm Standard board ) <sup>(*1)</sup>		
Dawer Dissipation	2227.24		150		
Power Dissipation	SSOT-24		500 (40mm x 40mm Standard board )(*1)	mW	
	007.05		250		
	SOT-25		600 (40mm x 40mm Standard board )(*1)		
Operating Temperature Range		Topr	-40~+85	°C	
Storage Te	mperature Range	Tstg	-55~+125	°C	

<sup>(\*1)</sup> The power dissipation figure shown is PCB mounted and is for reference only. The mounting condition is please refer to PACKAGING INFORMATION.

## **■**ELECTRICAL CHARACTERISTICS

XC6120 Series Ta=25°C

PARAM	METER	SYMBOL	CONDITION		MIN.	TYP.	MAX.	UNITS	CIRCUIT
Operating	g Voltage	VIN	V	DF(T)=1.0~5.0V (*1)	0.7	-	6.0	V	-
Detect	Voltage	$V_{DF}$	V	V <sub>DF(T)</sub> =1.0V∼5.0V		E-1		V	①
Hysteres	sis Width	V <sub>HYS</sub>	V <sub>DF(T)</sub> =1.0V∼5.0V		V <sub>DF</sub> × 0.03	V <sub>DF</sub> × 0.05	V <sub>DF</sub> × 0.07	V	1
Supply (	Current 1	I <sub>SS1</sub>		$V_{IN}=V_{DF(T)}\times 1.1$		E-2		μΑ	2
Supply (	Current 2	Iss2		$V_{IN}=V_{DF(T)}\times 0.9$		E-3		μΑ	2
Output	Current	I <sub>OUTN</sub>	$\begin{array}{c c} V_{\text{OUT}} = 0.5 V \\ \hline V_{\text{OUT}} = 0.3 V \\ \hline V_{\text{OUT}} = 0.1 V \\ \hline V_{\text{IN}} = 1.0 V & V_{\text{OUT}} = 0.1 V, V_{\text{DF}(T)} > 1.0 V \\ \hline V_{\text{IN}} = 2.0 V & V_{\text{OUT}} = 0.1 V, V_{\text{DF}(T)} > 2.0 V \\ \hline V_{\text{IN}} = 3.0 V & V_{\text{OUT}} = 0.1 V, V_{\text{DF}(T)} > 3.0 V \\ \hline V_{\text{IN}} = 4.0 V & V_{\text{OUT}} = 0.1 V, V_{\text{DF}(T)} > 4.0 V \\ \end{array}$		0.09 0.08 0.05 0.46	0.57 0.56 0.30 0.71		mA	3
					1.15 1.44 1.61	1.41 1.77 1.96	-		
		loutp (*2)	V <sub>IN</sub> =6.0V	V <sub>оит</sub> =5.5V	-	-0.95	-0.60	mA	3
Leakage Current	CMOS Output(Pch) N-ch Open Drain	ILEAK		$V_{IN}=V_{DF}\times0.9$ , $V_{OUT}=0V$ $V_{IN}=6.0V$ , $V_{OUT}=6.0V$		-0.001 0.001	0.10	μΑ	3
	erature teristics	Δ V <sub>DF</sub> / (Δ Topr • V <sub>DF</sub> )	-40 °C≦Topr≦85 °C		-	±100	-	ppm/°C	1
Detect Del	ay Time (*3)	t <sub>DF</sub>	$V_{IN}=6.0V\rightarrow0.7V$ $V_{IN}=V_{DF}$ to $V_{OUT}=0.5V$		-	30	100	μs	4
Release De	elay Time (*5)	t <sub>DR</sub>		V <sub>IN</sub> =0.7V→6.0V =V <sub>DR</sub> to V <sub>OUT</sub> =V <sub>DR</sub> (*4)	-	20	100	μs	4

 $<sup>^{(*1)}</sup>$ : V<sub>DF</sub> (T): Nominal detect voltage

#### ●XC6120N recommended pull-up resistance

Input Voltage Range	Pull-up Resistance
0.7V~6.0V	≧ 220kΩ
0.8V~6.0V	≧ 100kΩ
1.0V~6.0V	≧ 33kΩ

<sup>(\*2):</sup> For XC6120C only.

<sup>(\*3):</sup> A time taking from the time at  $V_{IN} = V_{DF}$  to the time at  $V_{OUT} = 0.5V$  when  $V_{IN}$  falls from 6.0V to 0.7V.

<sup>(\*4):</sup> V<sub>DR</sub>: Release voltage (V<sub>DR</sub> = V<sub>DF</sub> + V<sub>HYS</sub>)

<sup>(\*5):</sup> A time taking from the time at  $V_{IN} = V_{DR}$  to the time at  $V_{OUT} = V_{DR}$  when  $V_{IN}$  rise from 0.7V to 6.0V.

## ■ ELECTRICAL CHARACTERISTICS (Continued)

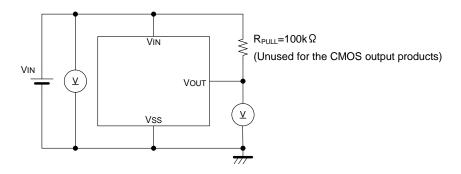
• DETECT VOLTAGE ACCURACY AND SUPPLY CURRENT SPECIFICATIONS

SYMBOL	E	-1	E	-2	E	-3
PARAMETER	DETECT	VOLTAGE				
	$V_{DF}$			SUPPLY CURRENT 1		URRENT 2
NOMINAL DETECT	XC6120xx	x2 Series	I <sub>SS1</sub> (	μΑ)	I <sub>SS2</sub> (	μA)
VOLTAGE		T		T		
V <sub>DF(T)</sub>	MIN.	MAX.	TYP.	MAX.	TYP.	MAX.
1.0	0.970	1.030	-			
1.1	1.070	1.130	_			
1.2	1.170	1.230	-			
1.3	1.270	1.330 1.430	+			
1.5	1.470	1.530	0.5	1.4	0.4	1.35
1.6	1.568	1.632	-			
1.7	1.666	1.734	-			
1.8	1.764	1.836	†			
1.9	1.862	1.938	1			
2.0	1.960	2.040				
2.1	2.058	2.142	1			
2.2	2.156	2.244	1			
2.3	2.254	2.346		4.7	0.5	4.00
2.4	2.352	2.448	0.6	1.7	0.5	1.60
2.5	2.450	2.550				
2.6	2.548	2.652				
2.7	2.646	2.754				
2.8	2.744	2.856				
2.9	2.842	2.958				
3.0	2.940	3.060	_			
3.1	3.038	3.162	_			
3.2	3.136	3.264	-			
3.3	3.234	3.366	_			
3.4	3.332	3.468	-			
3.5	3.430	3.570 3.672	+			
3.7	3.626	3.774	1			
3.8	3.724	3.876	-			
3.9	3.822	3.978	0.7	1.9	0.6	1.80
4.0	3.920	4.080	<del></del>	1.0		
4.1	4.018	4.182	1			
4.2	4.116	4.284	1			
4.3	4.214	4.386	1			
4.4	4.312	4.488	1			
4.5	4.410	4.590				
4.6	4.508	4.692				
4.7	4.606	4.794				
4.8	4.704	4.896				
4.9	4.802	4.998				
5.0	4.900	5.100				

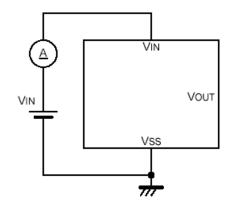
<sup>(°6)</sup>When detect voltage is  $1.0V \le V_{DF(T)} < 1.5V$ , detect accuracy is  $\pm 30$ mV. When detect voltage is  $1.5V \le V_{DF(T)} \le 5.0V$ , detect accuracy is  $\pm 2\%$ .

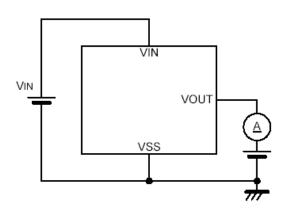
## **■**TEST CIRCUITS

#### Circuit ①

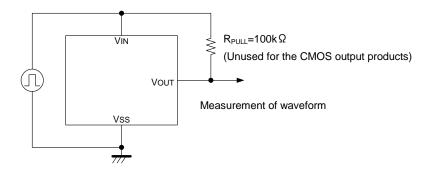


Circuit ② Circuit ③



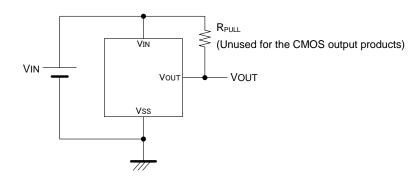


Circuit 4

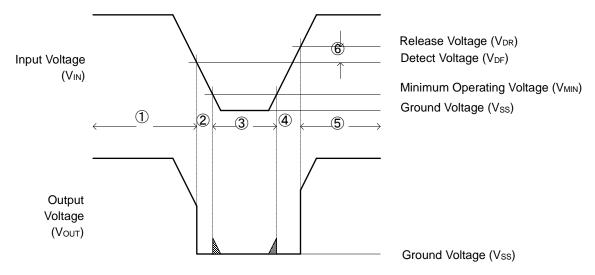


#### ■OPERATIONAL EXPLANATION

#### Typical Application Circuit



#### Timing Charge



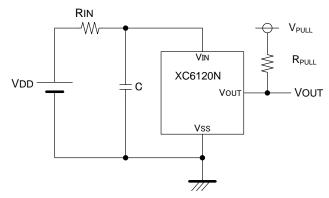
Note: For explaining in a simplified case, an operation time of the circuit is not counted.

The following explains the operation of the typical application circuit along number symbols shown in the timing chart.

- When input voltage (V<sub>IN</sub>) is higher than detect voltage (V<sub>DF</sub>), output voltage (V<sub>OUT</sub>) will be equal to input voltage (V<sub>IN</sub>).
   (A condition of high impedance exists with N-ch open drain output configurations.)
- ② When input voltage  $(V_{IN})$  falls below detect voltage  $(V_{DF})$ , output voltage  $(V_{OUT})$  will be equal to the ground voltage  $(V_{SS})$  level.
- ③ When input voltage (V<sub>IN</sub>) falls to a level below that of the minimum operating voltage (V<sub>MIN</sub>), output will become unstable. If In this condition, V<sub>IN</sub> will equal the pulled-up output (should output be pulled-up.) (Input voltage, V<sub>IN</sub>, in the typical application circuit.)
- When input voltage (V<sub>IN</sub>) rises above the minimum operating voltage (V<sub>MIN</sub>) level until it achieves a release voltage (V<sub>DR</sub>), output keeps the ground voltage level (V<sub>SS</sub>).
- (V<sub>IN</sub>). (A condition of high impedance exists with N-ch open drain output configurations.)
- 6 The difference between V<sub>DR</sub> and V<sub>DF</sub> represents the hysteresis width.

### ■NOTE ON USE

- 1. Please use this IC within the stated maximum ratings. For temporary, transitional voltage drop or voltage rising phenomenon, the IC is liable to malfunction should the ratings be exceeded.
- 2. In order to stabilize the IC's operations, please ensure that  $V_{IN}$  pin's input frequency's rise and fall times are more than several  $\mu$  s / V.
- 3. With a resistor connected between the V<sub>IN</sub> pin and the power supply V<sub>DD</sub> some errors may be observed from the input voltage at the detect and release voltage. Those errors are not constant because of the fluctuation of the supply current.
- 4. When a resistor is connected between the V<sub>IN</sub> pin and the power supply V<sub>DD</sub>, oscillation may occur as a result of through current and voltage drop at the R<sub>IN</sub> at the time of voltage release. (refer to the Oscillation Description (1) below ) Especially in the CMOS output configurations, oscillation may occur regardless of detect/release operation if load current (I<sub>OUT</sub>) exists. (refer to the Oscillation Description (2) below)
- 5. Please use N-ch open drains configuration, when a resistor R<sub>IN</sub> is connected between the V<sub>IN</sub> pin and the power supply V<sub>DD</sub> power source. In such cases, please ensure that R<sub>IN</sub> is less than  $10k\Omega$  and that C is more than  $0.1 \mu$  F.
- Torex places an importance on improving our products and its reliability.
   However, by any possibility, we would request user fail-safe design and post-aging treatment on system or equipment.



[Figure 1: Circuit connected with the input resistor]

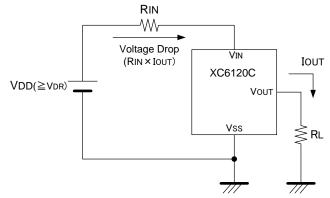
#### Oscillation Description

#### (1) Oscillation as a result of through current

Since the XC6120 series are CMOS ICs, transient through current will flow when the IC's internal circuit switching operates regardless of output configuration. Consequently, oscillation is liable to occur as a result of the similar operations as in (1) above. This oscillation does not occur during the detect operation.

#### (2) Output current oscillation with the CMOS output configuration

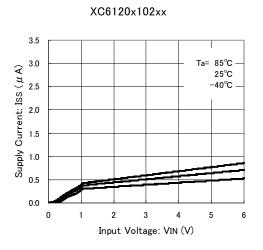
As shown in figure 2, when the voltage applied at the power supply  $(V_{DD})$  rises from below detect voltage to above release voltage, the IC commence release operations and the internal P-ch driver transistor will be on. The output current  $(I_{OUT})$  flows the input resistor  $(R_{IN})$  via the P-ch driver transistor. Because of the input resistor  $(R_{IN})$  and the output current  $(I_{OUT})$ , an input pin voltage drops  $R_{IN} \times I_{OUT}$ . If the voltage drop level is larger than the IC's hysteresis width  $(V_{HYS})$ , the input pin voltage will falls below the  $V_{DF}$  and detect operations will commerce so that the internal P-ch driver transistor will be off. The voltage drop will stop because the output current  $(I_{OUT})$  which was flowing the P-ch driver transistor will run down. The input pin voltage will become the same voltage level as the input voltage  $(V_{IN})$ . For this, the input pin voltage will rise above the release voltage  $(V_{DR})$ , therefore, the release operations will begin over again. Oscillation may occur with this repetition. Further, this condition will also appear via means of a similar mechanism during detect operations.

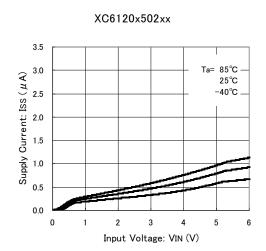


[Figure 2: Oscillation caused by the input resistor of the CMOS output product and the output current]

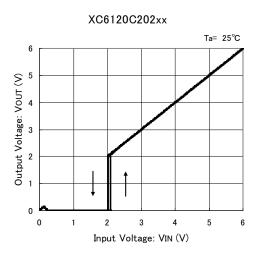
## **■TYPICAL PERFORMANCE CHARACTERISTICS**

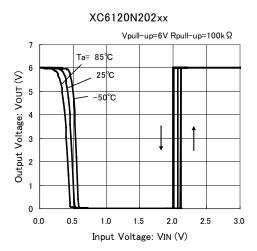
#### (1) Supply Current vs. Input Voltage



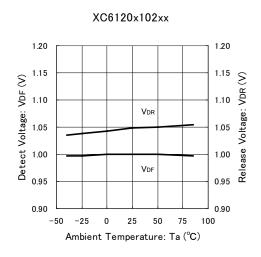


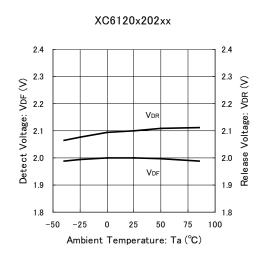
#### (2) Output Voltage vs. Input Voltage





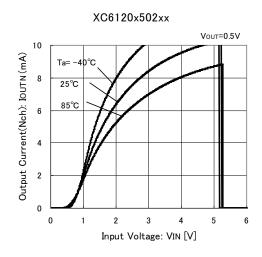
#### (3) Detect Voltage, Release Voltage vs. Ambient Temperature

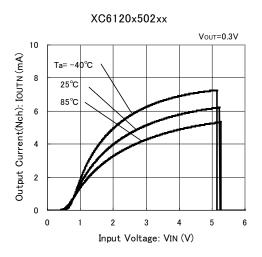




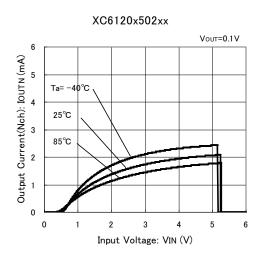
## ■TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

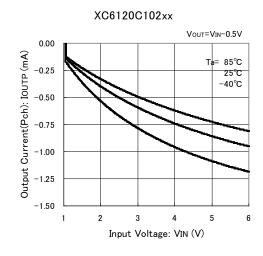
#### (4) Output Current (Nch Driver) vs. Input Voltage

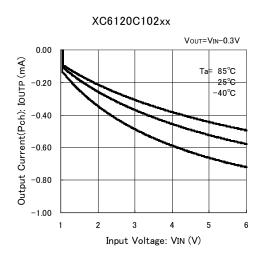


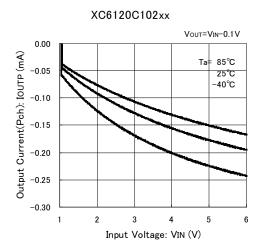


#### (5) Output Current (Pch Driver) vs. Input Voltage









# XC6120 Series

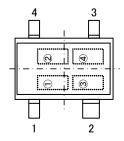
## **■**PACKAGING INFORMATION

For the latest package information go to, <a href="www.torexsemi.com/technical-support/packages">www.torexsemi.com/technical-support/packages</a>

PACKAGE	OUTLINE / LAND PATTERN	THERMAL CHARACTERISTICS			
SOT-25	SOT-25 PKG	Standard Board	SOT-25 Power Dissipation		
SSOT-24	SSOT-24 PKG	Standard Board	SSOT-24 Power Dissipation		
USP-3	<u>USP-3 PKG</u>	Standard Board	USP-3 Power Dissipation		

## ■ MARKING RULE

#### ●SSOT-24



① represents output configuration and detect voltage Range

MARK	OUTPUT CONFIGURATION	OUTPUT VOLTAGE	PRODUCT SERIES	
K	CMOS	1.0V~2.9V	VC6120C	
L	CIVIOS	3.0V~5.0V	XC6120C	
М	Nob open drain	1.0V~2.9V	XC6120N	
N	Nch open drain	3.0V~5.0V	AC0120N	

SSOT-24 (TOP VIEW)

2 represents detect voltage

MARK	DETECT V	OLTAGE (V)	MARK	DETECT V	OLTAGE (V)
0	-	3.0	F	1.5	4.5
1	-	3.1	Н	1.6	4.6
2	-	3.2	K	1.7	4.7
3	-	3.3	L	1.8	4.8
4	-	3.4	M	1.9	4.9
5	-	3.5	N	2.0	5.0
6	-	3.6	Р	2.1	-
7	-	3.7	R	2.2	-
8	-	3.8	S	2.3	-
9	-	3.9	Т	2.4	-
Α	1.0	4.0	U	2.5	-
В	1.1	4.1	V	2.6	-
С	1.2	4.2	X	2.7	-
D	1.3	4.3	Y	2.8	-
E	1.4	4.4	Z	2.9	-

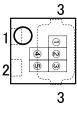
③, ④ represents production lot number

01 to 09, 10, 11, ..., 99, 0A, ..., 0Z, 1A, ...repeated.

(G, I, J, O, Q, W excluded. Reversed character is not used.)

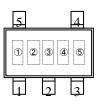
## ■ MARKING RULE (Continued)

#### ●USP-3



USP-3 (TOP VIEW)

●SOT-25



SOT-25 (TOP VIEW) ① represents product series

MARK	PRODUCT SERIES
0	XC6120*****

② standard : represents output configuration and integer number of detect voltage

● CMOS Output (XC6120C Series)

<ul><li>Nch open drain</li></ul>	(XC6120N Series)
----------------------------------	------------------

MARK	DETECT VOLTAGE (V)
Α	1.X
В	2.X
С	3.X
D	4.X
Е	5.X

MARK	DETECT VOLTAGE (V)
F	1.X
Н	2.X
K	3.X
L	4.X
М	5.X

3 standard : represents decimal point of detect voltage

MARK	DETECT VOLTAGE (V)	PRODUCT SERIES
3	X.3	XC6120**3***
0	X.0	XC6120**0***

④, ⑤ represents production lot number 01 to 09, 10, 11, ..., 99, 0A, ..., 0Z, 1A, ...repeated. (G, I, J, O, Q, W excluded.)

- 1. The product and product specifications contained herein are subject to change without notice to improve performance characteristics. Consult us, or our representatives before use, to confirm that the information in this datasheet is up to date.
- 2. The information in this datasheet is intended to illustrate the operation and characteristics of our products. We neither make warranties or representations with respect to the accuracy or completeness of the information contained in this datasheet nor grant any license to any intellectual property rights of ours or any third party concerning with the information in this datasheet.
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- 4. The product is neither intended nor warranted for use in equipment of systems which require extremely high levels of quality and/or reliability and/or a malfunction or failure which may cause loss of human life, bodily injury, serious property damage including but not limited to devices or equipment used in 1) nuclear facilities, 2) aerospace industry, 3) medical facilities, 4) automobile industry and other transportation industry and 5) safety devices and safety equipment to control combustions and explosions. Do not use the product for the above use unless agreed by us in writing in advance.
- 5. Although we make continuous efforts to improve the quality and reliability of our products; nevertheless Semiconductors are likely to fail with a certain probability. So in order to prevent personal injury and/or property damage resulting from such failure, customers are required to incorporate adequate safety measures in their designs, such as system fail safes, redundancy and fire prevention features.
- 6. Our products are not designed to be Radiation-resistant.
- 7. Please use the product listed in this datasheet within the specified ranges.
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TOREX SEMICONDUCTOR LTD.

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>>Torex Semiconductor(特瑞仕)